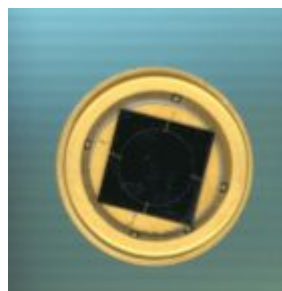


Large Active Area Si PIN Photo Diode IP-Si 3253Y

Characteristics:

- Large Active Area .
- Fast Response .
- Low Dark Current .
- High Responsivity .
- High Reliability .



Applications:

- Opto-Electronic Target Detecting System .
- 0.4-1.1 μ m Light Detection And OE
- ConveIPion System .
- Physical and Chemical Process Optical
- Detecting .

Mechanism:

Device works at reverse bias condition, and built as Si-PIN structure.

Technical Parameter(TA=23°C)

Parameter	Symbol	Test Conditions	Typical		Unit	
Active Area	Φ		10	10 II	mm	
Optical Parameter	Spectrum Response Range	λ	400~1100		nm	
	Responsivity	Re	$V_R=15V$ $\lambda=900nm$	0.5	0.43	A/W
			$V_R=15V$ $\lambda=0.6nm$	0.25	0.35	A/W
	Response Time	tr	$V_R=15V$ $R=50\Omega$	200	500	nS
Electrical Parameter	Dark Current	I_D	$V_R=15V$	100	100	nA
	Reverse Break Down Voltage	V_{BR}	$I_R=10\mu A$	80	50	V
	Capacitance	C_j	$f=1MHz$ $V_R=15V$	90	150	pF
Operating Voltage	V_R		5-40		V	
Package		TO-18				
Saturation Power $\leq 0.3w/cm^2$						

Typical Operating Characteristics

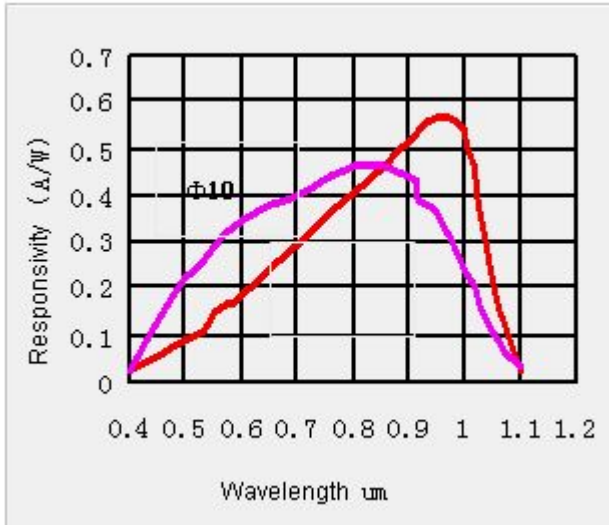


Fig. 1 Spectrum response curve

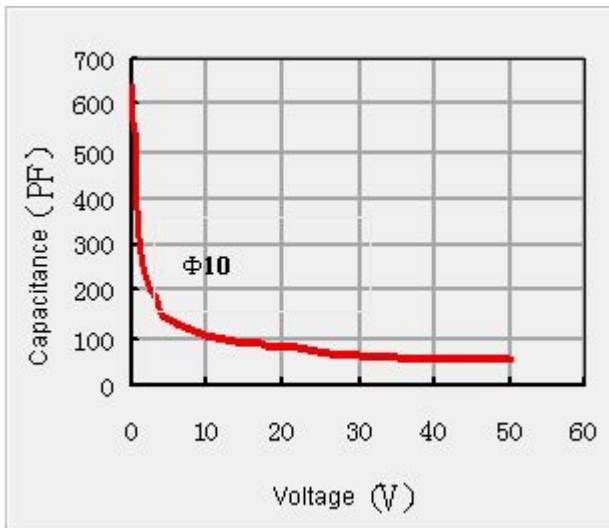
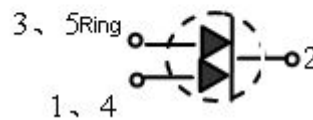
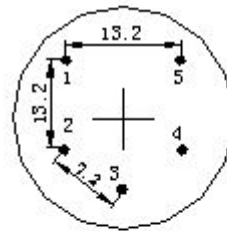
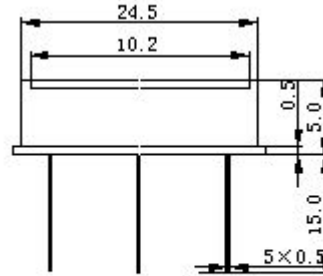


Fig. 2 C-V curve

Package Size and Application Method (Back side View)



7.Note

The device works under the reverse bias condition .

No Vibration and shock when device operating .

Static Charge Protection (Storage, Operating) .